

Title (en)
Method for forming pattern

Title (de)
Verfahren zur Herstellung eines Motivs

Title (fr)
Méthode pour former un motif

Publication
EP 0601887 B1 19960710 (EN)

Application
EP 93310002 A 19931210

Priority
• KR 920023805 A 19921210
• KR 930003210 A 19930304

Abstract (en)
[origin: EP0601887A1] A method for forming a pattern which improves a profile of a resist pattern. The method comprises the steps of forming a photoresist layer on a substrate (1) having a step, firstly exposing the photoresist layer using a first mask, secondly exposing a portion of the photoresist layer which is relatively thick due to the step using a second mask, and developing the exposed photoresist layer. Consequently, sufficient exposure is performed in a thick resist at the step portion, thereby to avoid the formation of a bridge or scum and obtaining a pattern having an improved profile. <IMAGE>

IPC 1-7
G03F 7/20

IPC 8 full level
G03F 7/26 (2006.01); **G03F 7/20** (2006.01); **H01L 21/027** (2006.01)

CPC (source: EP KR US)
G03F 1/70 (2013.01 - EP US); **G03F 7/04** (2013.01 - KR); **G03F 7/2022** (2013.01 - EP US); **G03F 7/703** (2013.01 - EP US)

Cited by
EP1288721A3; EP1280009A3; CN100458569C; EP0738925A3; CN102866581A; US6245492B1; WO2005062129A1; US6949330B2; US7349070B2

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0601887 A1 19940615; **EP 0601887 B1 19960710**; CN 1066829 C 20010606; CN 1089370 A 19940713; DE 69303585 D1 19960814; DE 69303585 T2 19970213; JP 3355239 B2 20021209; JP H06318541 A 19941115; KR 940015692 A 19940721; KR 950008384 B1 19950728; TW 234768 B 19941121; US 5413898 A 19950509

DOCDB simple family (application)
EP 93310002 A 19931210; CN 93120819 A 19931210; DE 69303585 T 19931210; JP 31088293 A 19931210; KR 930003210 A 19930304; TW 82110449 A 19931209; US 16488593 A 19931210